

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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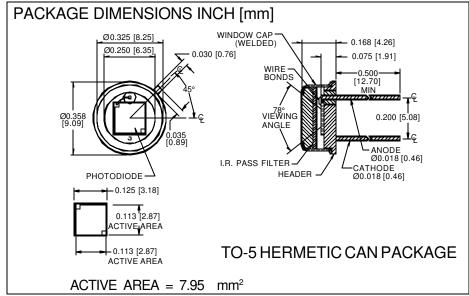




PHOTONIC DETECTORS INC

Silicon Photodiode, Near I.R. Photoconductive Type PDI-C119-F





FEATURES

- High speed
- Match to I.R. emitters
- Hermetic package

DESCRIPTION

The PDI-C119-F is a silicon, PIN planar • I.R. pass visible rejection diffused photodiode with NIR pass, visible light rejection optical filter. Ideal for high speed, low capacitance, photoconductive NIR applications. Packaged in a hermetic TO-5 metal can with a flat window cap.

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS
VBR	Reverse Voltage		100	V
T _{STG}	Storage Temperature	-55	+100	∘C
То	Operating Temperature Range	-40	+80	∘C
Ts	Soldering Temperature*		+240	∘C
I	Light Current		0.5	mA

^{*1/16} inch from case for 3 secs max

APPLICATIONS

- I.R. detector
- I.R. laser detector
- Photo-interrupters
- Industrial controls

SPECTRALRESPONSE

RESPONSIVITY (A/W) 0.5 0.3 0.2 0.1 190 300 400 500 600 700 800 WAVELENGTH(nm)

ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

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SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS			
Isc	Short Circuit Current	H = 100 fc, 2850 K	45	50		μιA			
ΙD	Dark Current	$H = 0, V_R = 10 V$		5	20	nA			
RsH	Shunt Resistance	$H = 0, V_R = 10 \text{ mV}$	150	300		MΩ			
TC Rsh	RSH Temp. Coefficient	$H = 0, V_R = 10 \text{ mV}$		-8		%/°C			
CJ	Junction Capacitance	$H = 0, V_R = 10 V^{**}$		60	150	рF			
λrange	Spectral Application Range	Spot Scan	700		1100	nm			
λр	Spectral Response - Peak	Spot Scan		950		nm			
V _{BR}	Breakdown Voltage	I = 10 µ A	75	100		V			
NEP	Noise Equivalent Power	V _R = 10 V @ Peak		5x10 ⁻¹⁴		W/√Hz			
tr	Response Time	$RL = 1 K\Omega V_p = 10 V$		50		nS			